New High-Speed CMOS Synchronous DRAMS with 128MB & 256MB Densities in 54-Ball TFBGA Package

Alliance Memory extended its 128M and 256M product range of high-speed CMOS synchronous DRAMs (SDRAM) with new devices in a 54-ball 8 x 8 x 1.2mm TFBGA package. These 8M x 16 and 16M x 16 SDRAMs feature fast access time from clock down to 4.5 ns at a 5-ns clock and clock rates of 143MHz.



The AS4C8M16S-7BCN and AS4C16M16S-7BCN is optimized for medical, industrial, automotive and telecom applications requiring high memory bandwidth. They are particularly well-suited to high-performance PC applications. These components operate from a single +3.3-V (± 0.3 V) power supply and are lead (Pb) and halogen-free.

Alliance Memory's legacy ICs provide reliable drop-in, pin-for-pin-compatible replacements for a number of similar solutions.

The AS4C8M16S-7BCN and AS4C16M16S-7BCN, the latest in their full line of high-speed SDRAMs – which include devices with densities of 16MB, 64MB, 128MB, 256MB and 512MB in the 54-pin TSOP II, 54-ball TFBGA, 86-pin TSOP II and 90-ball BGA packages.

Datasheets and additional information can be found on www.alliancememory.com